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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	65
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	81-UFBGA, WLCSP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476mgy6tr

List of tables

Table 1.	Device summary	1
Table 2.	STM32L476xx family device features and peripheral counts	13
Table 3.	Access status versus readout protection level and execution modes.	17
Table 4.	STM32L476 modes overview	22
Table 5.	Functionalities depending on the working mode.	27
Table 6.	STM32L476xx peripherals interconnect matrix	30
Table 7.	DMA implementation	35
Table 8.	Temperature sensor calibration values.	38
Table 9.	Internal voltage reference calibration values	38
Table 10.	Timer feature comparison.	43
Table 11.	I2C implementation.	47
Table 12.	STM32L4x6 USART/UART/LPUART features	48
Table 13.	SAI implementation.	51
Table 14.	Legend/abbreviations used in the pinout table	59
Table 15.	STM32L476xxSTM32L476xx pin definitions	60
Table 16.	Alternate function AF0 to AF7 (for AF8 to AF15 see Table 17)	73
Table 17.	Alternate function AF8 to AF15 (for AF0 to AF7 see Table 16)	80
Table 18.	STM32L476xx memory map and peripheral register boundary addresses	89
Table 19.	Voltage characteristics	95
Table 20.	Current characteristics	96
Table 21.	Thermal characteristics.	96
Table 22.	General operating conditions	97
Table 23.	Operating conditions at power-up / power-down	98
Table 24.	Embedded reset and power control block characteristics.	99
Table 25.	Embedded internal voltage reference.	101
Table 26.	Current consumption in Run and Low-power run modes, code with data processing running from Flash, ART enable (Cache ON Prefetch OFF)	104
Table 27.	Current consumption in Run and Low-power run modes, code with data processing running from Flash, ART disable	105
Table 28.	Current consumption in Run and Low-power run modes, code with data processing running from SRAM1	106
Table 29.	Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART enable (Cache ON Prefetch OFF)	107
Table 30.	Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART disable	108
Table 31.	Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1	108
Table 32.	Current consumption in Sleep and Low-power sleep modes, Flash ON	109
Table 33.	Current consumption in Low-power sleep modes, Flash in power-down	110
Table 34.	Current consumption in Stop 2 mode	110
Table 35.	Current consumption in Stop 1 mode	113
Table 36.	Current consumption in Stop 0 mode	115
Table 37.	Current consumption in Standby mode	116
Table 38.	Current consumption in Shutdown mode	117
Table 39.	Current consumption in VBAT mode	119
Table 40.	Peripheral current consumption	121
Table 41.	Low-power mode wakeup timings	124

[illegible]

Standby mode, supplied by the low-power Regulator (Standby with RAM2 retention mode).

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

The system clock after wakeup is MSI up to 8 MHz.

- **Shutdown mode**

The Shutdown mode allows to achieve the lowest power consumption. The internal regulator is switched off so that the VCORE domain is powered off. The PLL, the HSI16, the MSI, the LSI and the HSE oscillators are also switched off.

The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

SRAM1, SRAM2 and register contents are lost except for registers in the Backup domain.

The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper).

The system clock after wakeup is MSI at 4 MHz.

3.28 Low-power universal asynchronous receiver transmitter (LPUART)

The device embeds one Low-Power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock, and can wakeup the system from Stop mode. The wake up events from Stop mode are programmable and can be:

- Start bit detection
- Any received data frame
- A specific programmed data frame

Only a 32.768 kHz clock (LSE) is needed to allow LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
-	-	-	45	M11	67	PE14	I/O	FT	-	TIM1_CH4, TIM1_BKIN2, TIM1_BKIN2_COMP2, SPI1_MISO, QUADSPI_BK1_IO2, FMC_D11, EVENTOUT	-
-	-	-	46	M12	68	PE15	I/O	FT	-	TIM1_BKIN, TIM1_BKIN_COMP1, SPI1_MOSI, QUADSPI_BK1_IO3, FMC_D12, EVENTOUT	-
29	H3	H3	47	L10	69	PB10	I/O	FT_fl	-	TIM2_CH3, I2C2_SCL, SPI2_SCK, DFSDM_DATIN7, USART3_TX, LPUART1_RX, QUADSPI_CLK, LCD_SEG10, COMP1_OUT, SAI1_SCK_A, EVENTOUT	-
30	G3	G3	48	L11	70	PB11	I/O	FT_fl	-	TIM2_CH4, I2C2_SDA, DFSDM_CKIN7, USART3_RX, LPUART1_TX, QUADSPI_NCS, LCD_SEG11, COMP2_OUT, EVENTOUT	-
31	J2	J2	49	F12	71	VSS	S	-	-	-	-
32	J1	J1	50	G12	72	VDD	S	-	-	-	-
33	H1	H1	51	L12	73	PB12	I/O	FT_I	-	TIM1_BKIN, TIM1_BKIN_COMP2, I2C2_SMBA, SPI2_NSS, DFSDM_DATIN1, USART3_CK, LPUART1_RTS_DE, TSC_G1_IO1, LCD_SEG12, SWPMI1_IO, SAI2_FS_A, TIM15_BKIN, EVENTOUT	-

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
45	C1	C1	71	A12	104	PA12	I/O	FT_u	-	TIM1_ETR, USART1_RTS_DE, CAN1_TX, OTG_FS_DP, EVENTOUT	-
46	C2	C2	72	A11	105	PA13 (JTMS-SWDIO)	I/O	FT	(3)	JTMS-SWDIO, IR_OUT, OTG_FS_NOE, EVENTOUT	-
47	B1	B1	-	-	-	VSS	S	-	-	-	-
48	A1	A1	73	C11	106	VDDUSB	S	-	-	-	-
-	-	-	74	F11	107	VSS	S	-	-	-	-
-	-	-	75	G11	108	VDD	S	-	-	-	-
49	B2	B2	76	A10	109	PA14 (JTCK-SWCLK)	I/O	FT	(3)	JTCK-SWCLK, EVENTOUT	-
50	A2	A2	77	A9	110	PA15 (JTDI)	I/O	FT_I	(3)	JTDI, TIM2_CH1, TIM2_ETR, SPI1_NSS, SPI3_NSS, UART4_RTS_DE, TSC_G3_IO1, LCD_SEG17, SAI2_FS_B, EVENTOUT	-
51	D3	D3	78	B11	111	PC10	I/O	FT_I	-	SPI3_SCK, USART3_TX, UART4_TX, TSC_G3_IO2, LCD_COM4/LCD_SEG28/ LCD_SEG40, SDMMC1_D2, SAI2_SCK_B, EVENTOUT	-
52	C3	C3	79	C10	112	PC11	I/O	FT_I	-	SPI3_MISO, USART3_RX, UART4_RX, TSC_G3_IO3, LCD_COM5/LCD_SEG29/ LCD_SEG41, SDMMC1_D3, SAI2_MCLK_B, EVENTOUT	-
53	B3	B3	80	B10	113	PC12	I/O	FT_I	-	SPI3_MOSI, USART3_CK, UART5_TX, TSC_G3_IO4, LCD_COM6/LCD_SEG30/ LCD_SEG42, SDMMC1_CK, SAI2_SD_B, EVENTOUT	-
-	-	-	81	C9	114	PD0	I/O	FT	-	SPI2_NSS, DFSDM_DATIN7, CAN1_RX, FMC_D2, EVENTOUT	-

Table 17. Alternate function AF8 to AF15 (for AF0 to AF7 see [Table 16](#)) (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4, UART5, LPUART1	CAN1, TSC	OTG_FS, QUADSPI	LCD	SDMMC1, COMP1, COMP2, FMC, SWPMI1	SAI1, SAI2	TIM2, TIM15, TIM16, TIM17, LPTIM2	EVENTOUT
Port C	PC0	LPUART1_RX	-	-	LCD_SEG18	-	-	LPTIM2_IN1	EVENTOUT
	PC1	LPUART1_TX	-	-	LCD_SEG19	-	-	-	EVENTOUT
	PC2	-	-	-	LCD_SEG20	-	-	-	EVENTOUT
	PC3	-	-	-	LCD_VLCD	-	SAI1_SD_A	LPTIM2_ETR	EVENTOUT
	PC4	-	-	-	LCD_SEG22	-	-	-	EVENTOUT
	PC5	-	-	-	LCD_SEG23	-	-	-	EVENTOUT
	PC6	-	TSC_G4_IO1	-	LCD_SEG24	SDMMC1_D6	SAI2_MCLK_A	-	EVENTOUT
	PC7	-	TSC_G4_IO2	-	LCD_SEG25	SDMMC1_D7	SAI2_MCLK_B	-	EVENTOUT
	PC8	-	TSC_G4_IO3	-	LCD_SEG26	SDMMC1_D0	-	-	EVENTOUT
	PC9	-	TSC_G4_IO4	OTG_FS_NOE	LCD_SEG27	SDMMC1_D1	SAI2_EXTCLK	TIM8_BKIN2_COMP1	EVENTOUT
	PC10	UART4_TX	TSC_G3_IO2	-	LCD_COM4/ LCD_SEG28/ LCD_SEG40	SDMMC1_D2	SAI2_SCK_B	-	EVENTOUT
	PC11	UART4_RX	TSC_G3_IO3	-	LCD_COM5/ LCD_SEG29/ LCD_SEG41	SDMMC1_D3	SAI2_MCLK_B	-	EVENTOUT
	PC12	UART5_TX	TSC_G3_IO4	-	LCD_COM6/ LCD_SEG30/ LCD_SEG42	SDMMC1_CK	SAI2_SD_B	-	EVENTOUT
	PC13	-	-	-	-	-	-	-	EVENTOUT
	PC14	-	-	-	-	-	-	-	EVENTOUT
	PC15	-	-	-	-	-	-	-	EVENTOUT

Table 29. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART enable (Cache ON Prefetch OFF)

Symbol	Parameter	Conditions			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
$I_{DD}(\text{Run})$	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 $f_{HCLK} = 26 \text{ MHz}$	Reduced code ⁽¹⁾	2.9	mA	111	$\mu\text{A}/\text{MHz}$
				Coremark	3.1		118	
				Dhrystone 2.1	3.1		119	
				Fibonacci	2.9		112	
				While(1)	2.8		108	
			Range 1 $f_{HCLK} = 80 \text{ MHz}$	Reduced code ⁽¹⁾	10.2	mA	127	$\mu\text{A}/\text{MHz}$
				Coremark	10.9		136	
				Dhrystone 2.1	11.0		137	
				Fibonacci	10.5		131	
				While(1)	9.9		124	
$I_{DD}(\text{LPRun})$	Supply current in Low-power run	$f_{HCLK} = f_{MSI} = 2 \text{ MHz}$ all peripherals disable		Reduced code ⁽¹⁾	272	μA	136	$\mu\text{A}/\text{MHz}$
				Coremark	291		145	
				Dhrystone 2.1	302		151	
				Fibonacci	269		135	
				While(1)	269		135	

1. Reduced code used for characterization results provided in [Table 26](#), [Table 27](#), [Table 28](#).

Table 39. Current consumption in VBAT mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{BAT}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (VBAT)	Backup domain supply current	RTC disabled	1.8 V	4	29	196	587	1663	10.8	73	490	1468	4158	nA
			2.4 V	5.27	36	226	673	1884	13.2	90	565	1683	4710	
			3 V	6	42	264	775	2147	15.5	106	660	1938	5368	
			3.6 V	10	58	323	919	2488	25.8	144	808	2298	6220	
		RTC enabled and clocked by LSE bypassed at 32768 Hz	1.8 V	183	201	367	729	-	-	-	-	-	-	
			2.4 V	268	295	486	901	-	-	-	-	-	-	
			3 V	376	412	602	1075	-	-	-	-	-	-	
			3.6 V	508	558	752	1299	-	-	-	-	-	-	
		RTC enabled and clocked by LSE quartz ⁽²⁾	1.8 V	302	344	521	915	1978	-	-	-	-	-	
			2.4 V	388	436	639	1091	2289	-	-	-	-	-	
			3 V	494	549	784	1301	2656	-	-	-	-	-	
			3.6 V	630	692	971	1571	3115	-	-	-	-	-	

1. Guaranteed by characterization results, unless otherwise specified.

2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

Table 42. Regulator modes transition times⁽¹⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WULPRUN}$	Wakeup time from Low-power run mode to Run mode ⁽²⁾	Code run with MSI 2 MHz	5	7	μs
t_{VOST}	Regulator transition time from Range 2 to Range 1 or Range 1 to Range 2 ⁽³⁾	Code run with MSI 24 MHz	20	40	

1. Guaranteed by characterization results.

2. Time until REGLPF flag is cleared in PWR_SR2.

3. Time until VOSF flag is cleared in PWR_SR2.

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

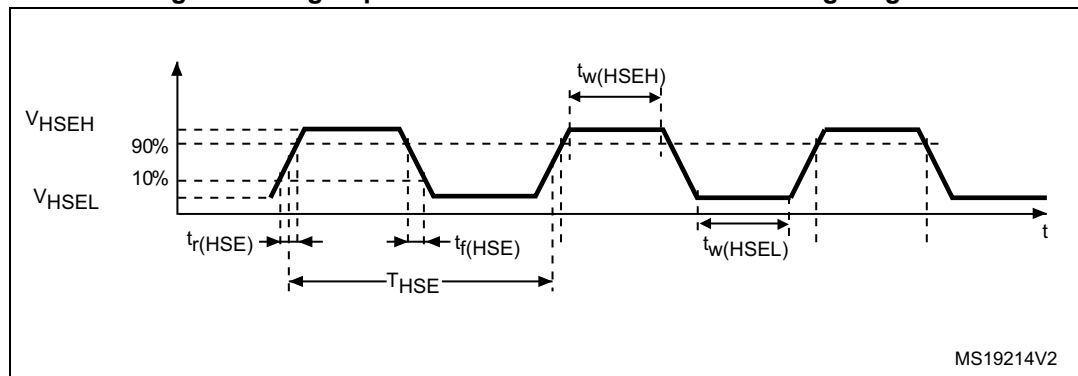
The external clock signal has to respect the I/O characteristics in [Section 6.3.14](#). However, the recommended clock input waveform is shown in [Figure 16: High-speed external clock source AC timing diagram](#).

Table 43. High-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	Voltage scaling Range 1	-	8	48	MHz
		Voltage scaling Range 2	-	8	26	
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7 V_{DDIOx}$	-	V_{DDIOx}	V
V_{HSEL}	OSC_IN input pin low level voltage	-	V_{SS}	-	$0.3 V_{DDIOx}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time	Voltage scaling Range 1	7	-	-	ns
		Voltage scaling Range 2	18	-	-	

1. Guaranteed by design.

Figure 16. High-speed external clock source AC timing diagram



6.3.8 Internal clock source characteristics

The parameters given in [Table 47](#) are derived from tests performed under ambient temperature and supply voltage conditions summarized in [Table 22: General operating conditions](#). The provided curves are characterization results, not tested in production.

High-speed internal (HSI16) RC oscillator

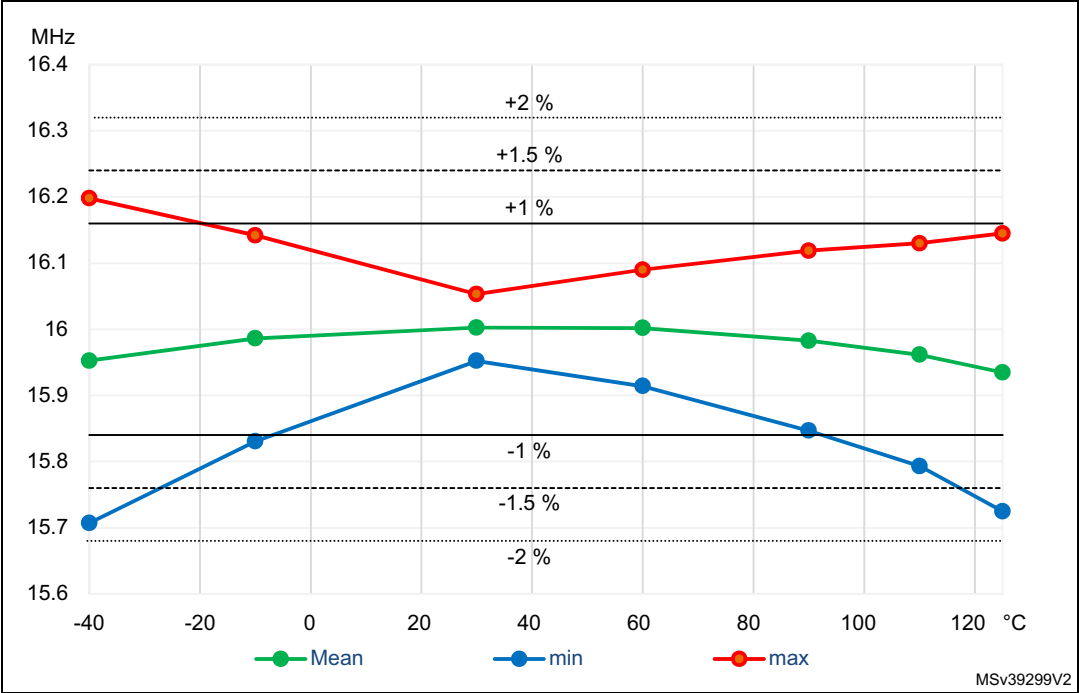
Table 47. HSI16 oscillator characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI16}	HSI16 Frequency	$V_{\text{DD}}=3.0\text{ V}$, $T_{\text{A}}=30\text{ }^{\circ}\text{C}$	15.88	-	16.08	MHz
TRIM	HSI16 user trimming step	Trimming code is not a multiple of 64	0.2	0.3	0.4	%
		Trimming code is a multiple of 64	-4	-6	-8	
$\text{DuCy}(\text{HSI16})^{(2)}$	Duty Cycle	-	45	-	55	%
$\Delta_{\text{Temp}}(\text{HSI16})$	HSI16 oscillator frequency drift over temperature	$T_{\text{A}}=0\text{ to }85\text{ }^{\circ}\text{C}$	-1	-	1	%
		$T_{\text{A}}=-40\text{ to }125\text{ }^{\circ}\text{C}$	-2	-	1.5	%
$\Delta_{\text{VDD}}(\text{HSI16})$	HSI16 oscillator frequency drift over V_{DD}	$V_{\text{DD}}=1.62\text{ V to }3.6\text{ V}$	-0.1	-	0.05	%
$t_{\text{su}}(\text{HSI16})^{(2)}$	HSI16 oscillator start-up time	-	-	0.8	1.2	μs
$t_{\text{stab}}(\text{HSI16})^{(2)}$	HSI16 oscillator stabilization time	-	-	3	5	μs
$I_{\text{DD}}(\text{HSI16})^{(2)}$	HSI16 oscillator power consumption	-	-	155	190	μA

1. Guaranteed by characterization results.

2. Guaranteed by design.

Figure 20. HSI16 frequency versus temperature



Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 56. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A ⁽¹⁾

1. Negative injection is limited to -30 mA for PF0, PF1, PG6, PG7, PG8, PG12, PG13, PG14.

6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DDIOx} (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the $-5\text{ }\mu\text{A}/+0\text{ }\mu\text{A}$ range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in [Table 57](#).

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Table 57. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0 pin	-0	NA ⁽¹⁾	mA
	Injected current on pins except PA4, PA5, BOOT0	-5	NA ⁽¹⁾	
	Injected current on PA4, PA5 pins	-5	0	

1. NA: not applicable

Table 60. I/O AC characteristics⁽¹⁾⁽²⁾

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	5	MHz
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	1	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	0.1	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	10	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	1.5	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	25	ns
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	52	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	140	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	17	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	37	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	25	MHz
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	10	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	1	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	50	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	15	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	9	ns
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	16	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	40	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	4.5	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	9	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	21	

6.3.17 Analog-to-Digital converter characteristics

Unless otherwise specified, the parameters given in [Table 63](#) are preliminary values derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in [Table 22: General operating conditions](#).

Note: *It is recommended to perform a calibration after each power-up.*

Table 63. ADC characteristics^{(1) (2)}

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-	1.62	-	3.6	V
$V_{\text{REF+}}$	Positive reference voltage	$V_{\text{DDA}} \geq 2 \text{ V}$	2	-	V_{DDA}	V
		$V_{\text{DDA}} < 2 \text{ V}$	V_{DDA}			V
$V_{\text{REF-}}$	Negative reference voltage	-	V_{SSA}			V
f_{ADC}	ADC clock frequency	Range 1	-	-	80	MHz
		Range 2	-	-	26	
f_{s}	Sampling rate for FAST channels	Resolution = 12 bits	-	-	5.33	MSPS
		Resolution = 10 bits	-	-	6.15	
		Resolution = 8 bits	-	-	7.27	
		Resolution = 6 bits	-	-	8.88	
	Sampling rate for SLOW channels	Resolution = 12 bits	-	-	4.21	
		Resolution = 10 bits	-	-	4.71	
		Resolution = 8 bits	-	-	5.33	
		Resolution = 6 bits	-	-	6.15	
f_{TRIG}	External trigger frequency	$f_{\text{ADC}} = 80 \text{ MHz}$ Resolution = 12 bits	-	-	5.33	MHz
		Resolution = 12 bits	-	-	15	$1/f_{\text{ADC}}$
$V_{\text{AIN}}^{(3)}$	Conversion voltage range(2)	-	0	-	$V_{\text{REF+}}$	V
R_{AIN}	External input impedance	-	-	-	50	k Ω
C_{ADC}	Internal sample and hold capacitor	-	-	5	-	pF
t_{STAB}	Power-up time	-	1			conversion cycle
t_{CAL}	Calibration time	$f_{\text{ADC}} = 80 \text{ MHz}$	1.45			μs
		-	116			$1/f_{\text{ADC}}$
t_{LATR}	Trigger conversion latency Regular and injected channels without conversion abort	CKMODE = 00	1.5	2	2.5	$1/f_{\text{ADC}}$
		CKMODE = 01	-	-	2.0	
		CKMODE = 10	-	-	2.25	
		CKMODE = 11	-	-	2.125	

Table 65. ADC accuracy - limited test conditions 1⁽¹⁾(2)(3) (continued)

Sym- bol	Parameter	Conditions ⁽⁴⁾			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency $\leq$ 80 MHz, Sampling rate $\leq$ 5.33 Msps, $V_{DDA} = V_{REF+} = 3$ V, $T_A = 25$ °C	Single ended	Fast channel (max speed)	-	-74	-73	dB
				Slow channel (max speed)	-	-74	-73	
			Differential	Fast channel (max speed)	-	-79	-76	
				Slow channel (max speed)	-	-79	-76	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when $V_{DDA} < 2.4$ V (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{DDA} < 2.4$ V). It is disable when $V_{DDA} \geq 2.4$ V. No oversampling.

Table 94. Asynchronous multiplexed PSRAM/NOR read timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}-0.5$	$3T_{HCLK}+2$	ns
$t_{v(NOE_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	
$t_{w(NOE)}$	FMC_NOE low time	$T_{HCLK}+0.5$	$T_{HCLK}+1$	
$t_{h(NE_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A_NE)}$	FMC_NEx low to FMC_A valid	-	3	
$t_{v(NADV_NE)}$	FMC_NEx low to FMC_NADV low	0	1	
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+1$	
$t_{h(AD_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high	0	-	
$t_{h(A_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK}-0.5$	-	
$t_{h(BL_NOE)}$	FMC_BL time after FMC_NOE high	0	-	
$t_{v(BL_NE)}$	FMC_NEx low to FMC_BL valid	-	2	
$t_{su(Data_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}-2$	-	
$t_{su(Data_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}-1$	-	
$t_{h(Data_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{h(Data_NOE)}$	Data hold time after FMC_NOE high	0	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

Table 95. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+2$	$8T_{HCLK}+4$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}-1$	$5T_{HCLK}+1.5$	
$t_{su(NWAIT_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+1.5$	-	
$t_{h(NE_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$	-	

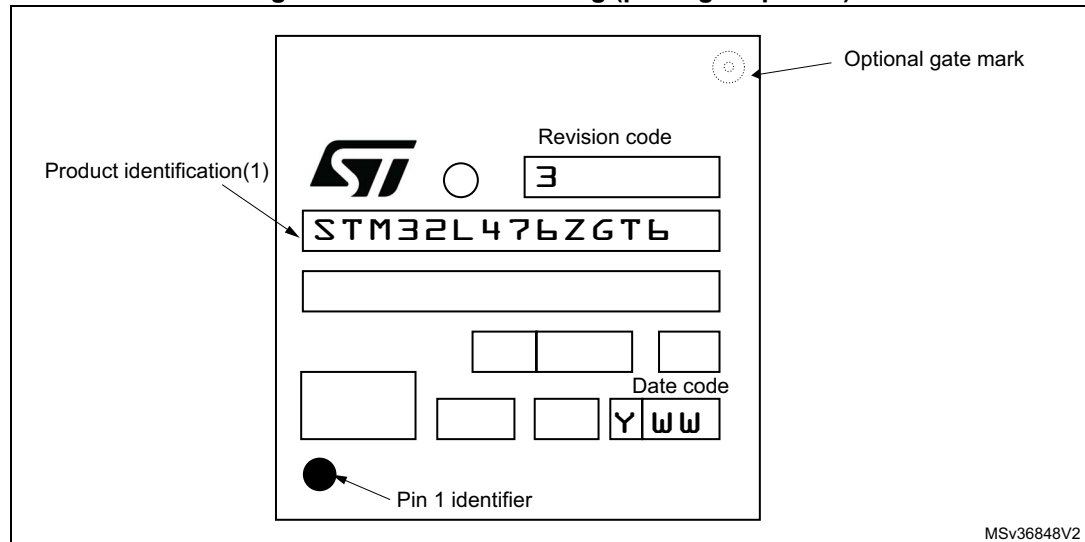
1. CL = 30 pF.

2. Guaranteed by characterization results.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 51. LQFP144 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

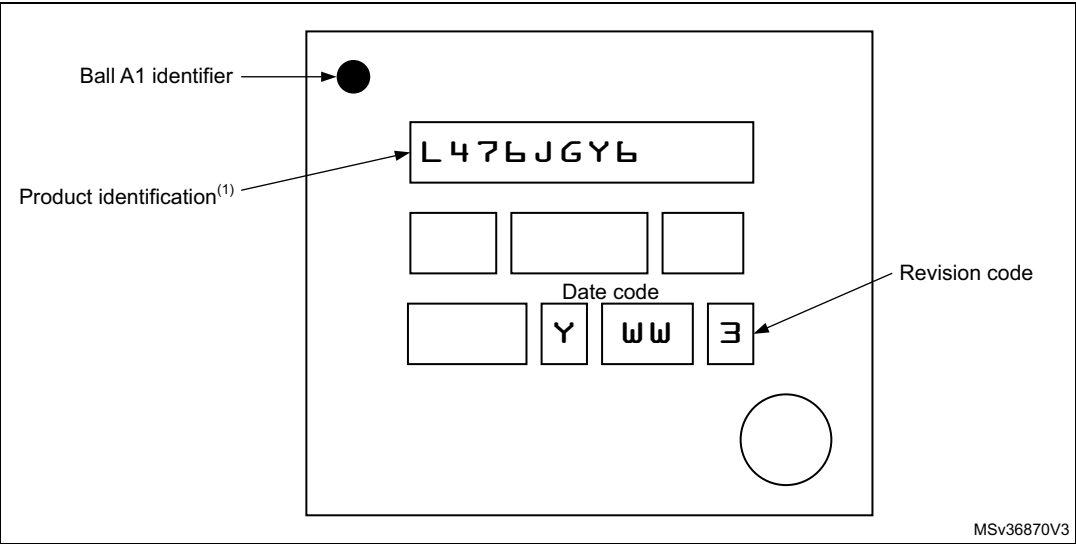
Table 111. WLCSP72 recommended PCB design rules (0.4 mm pitch BGA)

Dimension	Recommended values
Pitch	0.4 mm
Dpad	0.225 mm
Dsm	0.290 mm typ. (depends on the solder mask registration tolerance)
Stencil opening	0.250 mm
Stencil thickness	0.100 mm

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 63. WLCSP72 marking (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

8 Part numbering

Table 114. STM32L476xx ordering information scheme

Example:	STM32	L	476	R	G	T	6	TR
Device family								
STM32 = ARM [®] based 32-bit microcontroller								
Product type								
L = ultra-low-power								
Device subfamily								
476: STM32L476xx								
Pin count								
R = 64 pins								
J = 72 pins								
M = 81 pins								
V = 100 pins								
Q = 132 pins								
Z = 144 pins								
Flash memory size								
C = 256 KB of Flash memory								
E = 512 KB of Flash memory								
G = 1 MB of Flash memory								
Package								
T = LQFP ECOPACK [®] 2								
I = UFBGA ECOPACK [®] 2								
Y = CSP ECOPACK [®] 2								
Temperature range								
6 = Industrial temperature range, -40 to 85 °C (105 °C junction)								
7 = Industrial temperature range, -40 to 105 °C (125 °C junction)								
3 = Industrial temperature range, -40 to 125 °C (130 °C junction)								
Packing								
TR = tape and reel								
xxx = programmed parts								